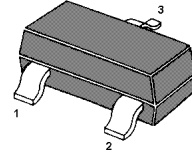
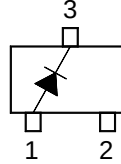


SDB505S

Silicon Epitaxial Planar Schottky Barrier Diode

High frequency rectification



Marking Code: **ES**
TO-236 Plastic Package

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	50	V
Reverse Voltage	V_R	50	V
Average Forward Current	$I_{F(AV)}$	500	mA
Non-repetitive Peak Surge Current	I_{FSM}	5	A
Junction Temperature	T_j	125	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 125	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit
Reverse Voltage at $I_R = 200\ \mu\text{A}$	V_R	50	-	-	V
Forward Voltage at $I_F = 500\ \text{mA}$	V_F	-	-	0.55	V
Reverse Current at $V_R = 25\ \text{V}$	I_R	-	-	20	μA
Total Capacitance at $V_R = 10\ \text{V}$, $f = 1\ \text{MHz}$	C_T	-	22	-	pF

